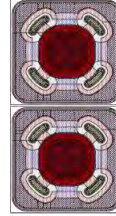


Wafer Information

Item	Description
Wafer Size	6 inch (150mm)
Wafer Thickness	150um ± 10um
Die Size (with scribe lane)	334um x 186um
Bond Pad Opening	71um x 71um
Scribe Lane Width	40um
Gross Die Per Wafer	250,000
Top Metal (for wire bond)	4µm AlSiCu
Backside Metal (for die bond)	N/A

Die Appearance



Circuit Diagram



- Complies with IEC 61000-4-2 standards:
Contact discharge: ±20kV

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	72	W
Peak Pulse Current (8/20µs)	IPP	4	A
Operating Temperature Range	T_J	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6.0			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			100	nA	VRWM = 5V
Clamping Voltage	VC		10		V	IPP = 1A (8 x 20µs pulse)
Clamping Voltage	VC		18		V	IPP = 4A (8 x 20µs pulse)
Junction Capacitance	C_J		0.25	0.35	pF	VR = 0V, f = 1MHz

Note: Electrical parameters are only for die, performance may alter after assembly.

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